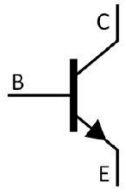
TO-220F NPN Silicon NPN transistor in a TO-220F Plastic Package.

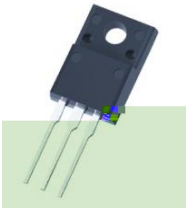
h_{FE}

High h_{FE}, good linearity of h_{FE}.

h_{FE}

Power amplifier with high forward current transfer ratio applications.

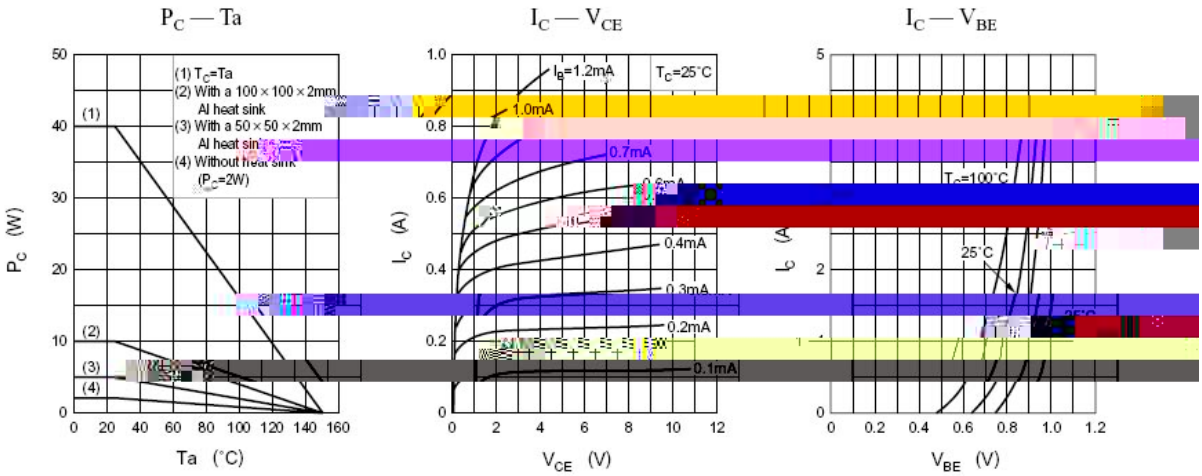


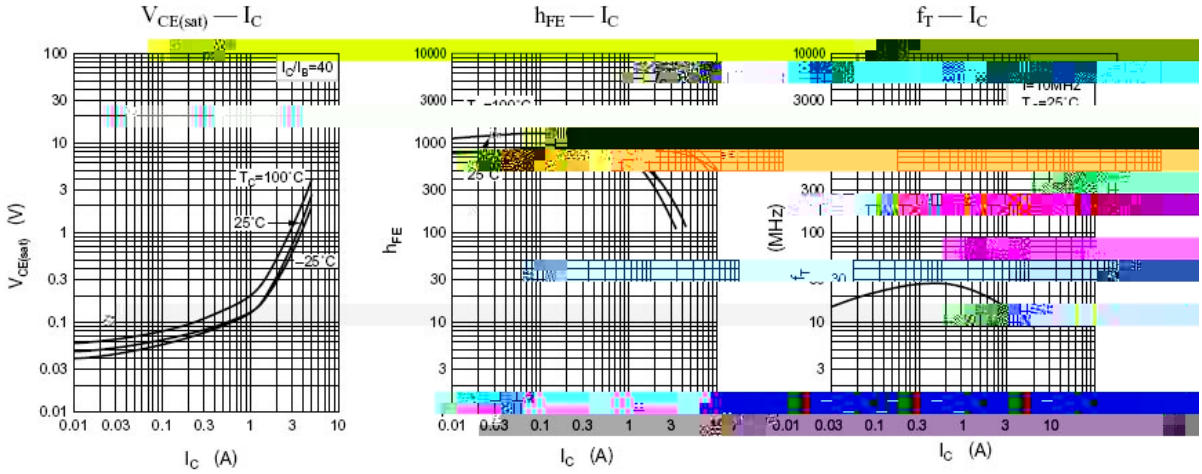


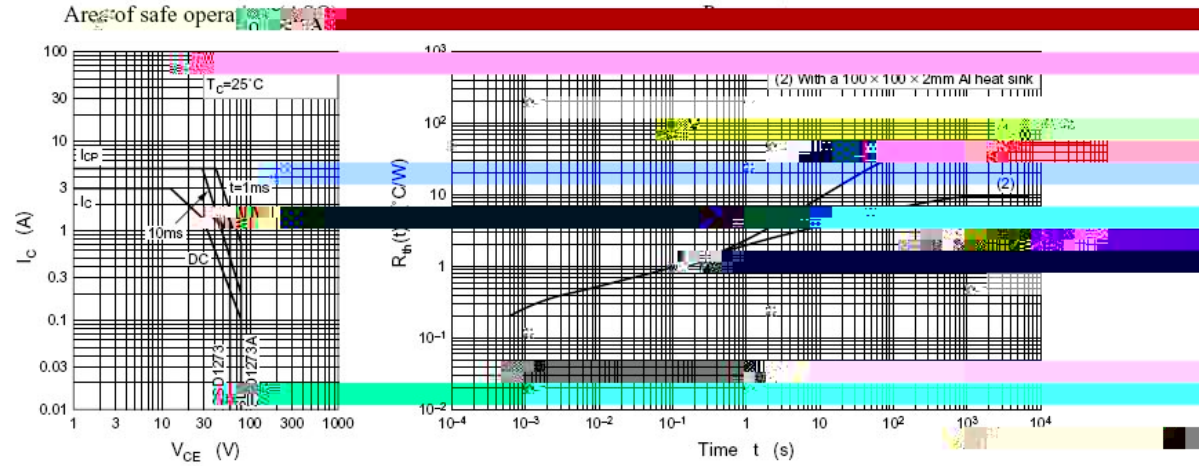
PIN1 Base PIN 2 Collector PIN 3 Emitter

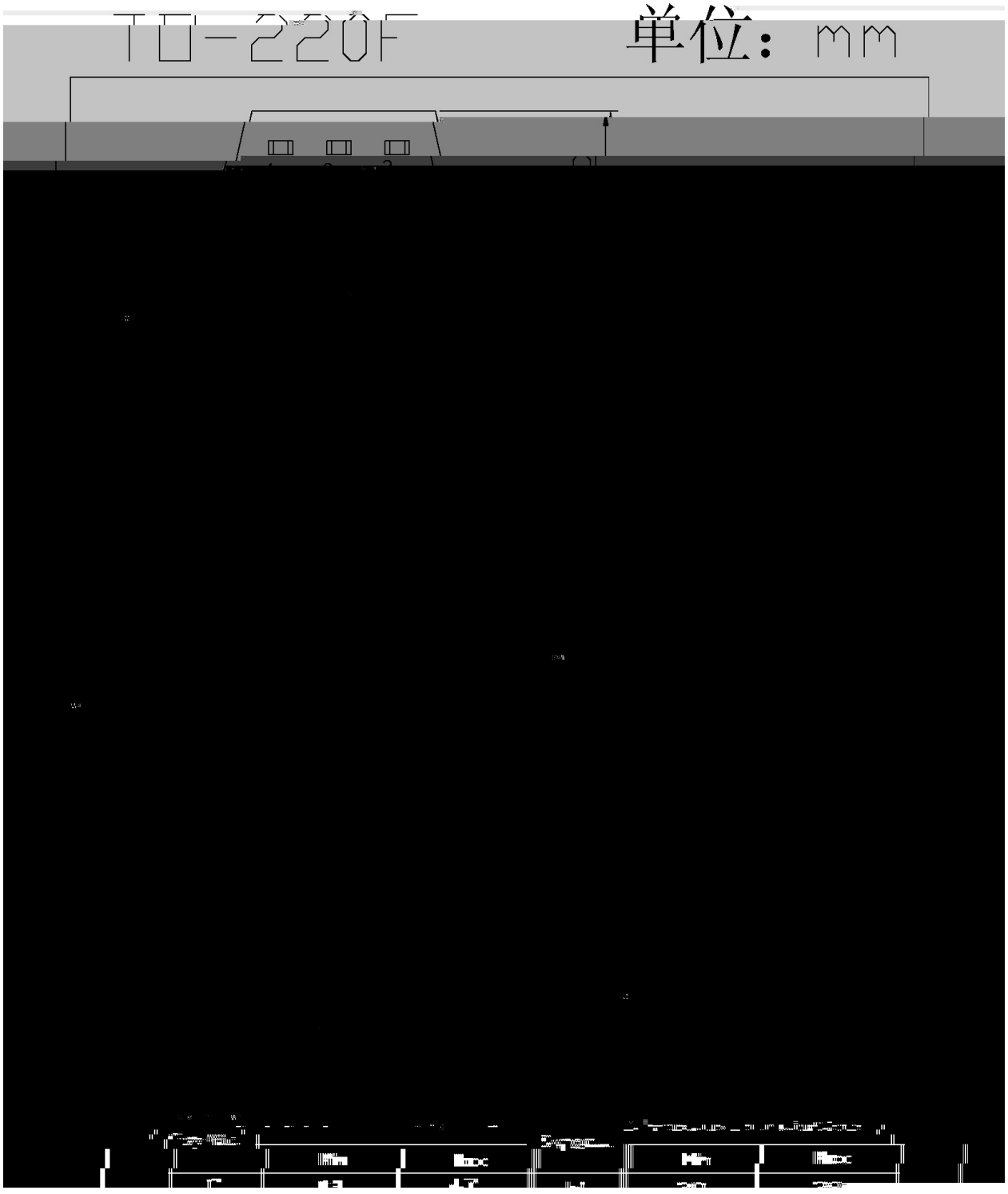
h_{FE} Classifications Symbol	Q	P	O
h_{FE} Range	500 1000	800 1500	1200 2500

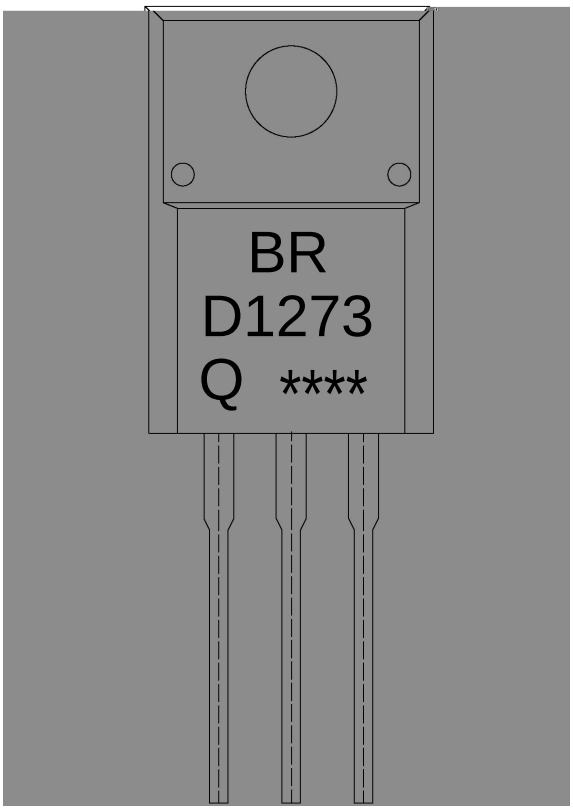
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SD1273	80	V
		2SD1273A	100	
Collector to Emitter Voltage	V_{CEO}	2SD1273	60	


P_C — Ta
(1) T_C=Ta
(2) With a 100×100×2mm Al heat sink
(3) With a 50×50×2mm Al heat sink
(4) Without heat sink (P_C=2W)
P_C (W)
Ta (°C)
I_C — V_{CE}
I_B=1.2mA
1.0mA
0.7mA
0.4mA
0.3mA
0.2mA
0.1mA
T_C=25°C
I_C (A)
V_{CE} (V)
I_C — V_{BE}
T_C=100°C
25°C
I_C (A)
V_{BE} (V)


$V_{CE(sat)}$ — I_C
I_C/I_B=40
T_C=100°C
25°C
−25°C
$V_{CE(sat)}$ (V)
I_C (A)
h_{FE} — I_C
25°C
h_{FE}
I_C (A)
f_T — I_C
f=10MHz
T_C=25°C
f_T (MHz)
I_C (A)


Area of safe operation
T_C=25°C
I_{CP}
I_C
t=1ms
10ms
DC
I_C (A)
V_{CE} (V)
(2) With a 100×100×2mm Al heat sink
$R_{th(t)}$ (°C/W)
Time t (s)


TO-220F
单位：mm



BR

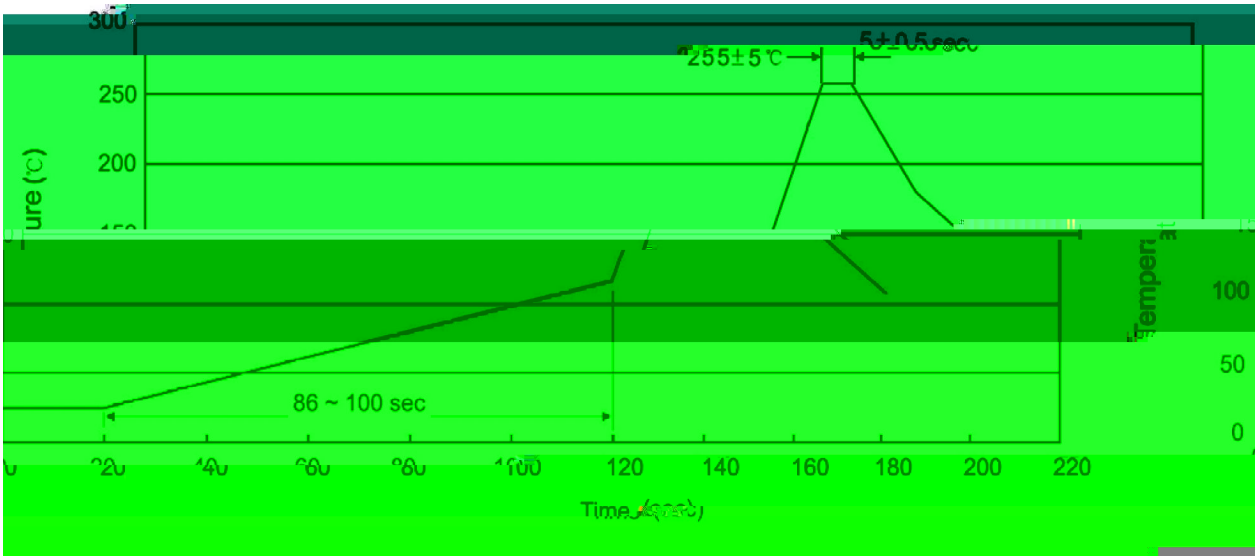
D1273

Q: h_{FE}

****

Note:

BR:	Company Code.
D1273:	Product Type.
Q:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.



								Note:	
1		25	150			60	90sec;	1.Preheating:25~150	, Time:60~90sec.
2		255±5					5±0.5sec;	2.Peak Temp.:255±5	, Duration:5±0.5sec.
3				2	10	/sec.		3. Cooling Speed: 2~10	/sec.

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ BULK

Package Type	Units			Dimension (unit mm^3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box	